

Appl. No. 10/692,406  
Amdt. Dated May 9, 2005  
Reply to Office Action of March 21, 2003

Attorney Docket No. 81707.0189  
Customer No.: 26021

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Canceled)
2. (Currently amended) A glass ceramic sintered body according to claim ~~[[1]]~~ 8, wherein the flexural strength is not smaller than 150 MPa.
3. (Currently amended) A glass ceramic sintered body according to claim ~~[[1]]~~ 8, ~~wherein the content of comprising PbO not larger than 0.1 mass % and the content of an alkali metal oxide are not larger than 0.1 mass %, respectively.~~
4. (Currently amended) A glass ceramic sintered body according to claim ~~[[1]]~~ 8, further ~~containing~~ comprising at least one of those selected from the group consisting of alumina, spinel, mullite, anorthite, slawsonite, celsian and ~~zirconia~~ zirconia, as a crystal phase.
5. (Canceled)
6. (Currently amended) A glass ceramic sintered body according to claim ~~[[5]]~~ 8, ~~containing~~ comprising a cordierite crystal phase in an amount of not smaller than 20 mass % and having a thermal expansion coefficient at 40 to 400°C of not larger than  $4.5 \times 10^{-6}/^{\circ}\text{C}$ .
7. (Original) A glass ceramic sintered body according to claim 6, by using, as said filler powder, at least one inorganic powder for adjusting properties selected

Appl. No. 10/692,406  
Amdt. Dated May 9, 2005  
Reply to Office Action of March 21, 2003

Attorney Docket No. 81707.0189  
Customer No.: 26021

from the group consisting of mullite, anorthite, slawsonite, celsian and quartz glass, and further using a cordierite powder.

8. (Currently amended) A glass ceramic sintered body ~~according to claim 5~~ comprising gahnite and cordierite as crystal phases, having a thermal expansion coefficient at 40 to 400°C of not larger than  $5 \times 10^{-6}/^{\circ}\text{C}$ , a dielectric constant of not larger than 7 and a Young's modulus of not larger than 150 GPa, obtained by firing a mixed powder of a glass powder having the following composition:

SiO<sub>2</sub>: 30 to 55 mass %

Al<sub>2</sub>O<sub>3</sub>: 15 to 40 mass %

MgO: 3 to 25 mass %

ZnO: 2 to 15 mass %

B<sub>2</sub>O<sub>3</sub>: 2 to 15 mass %

and a filler powder, wherein the glass ceramic sintered body further comprises having a CaO-containing glass phase.

9. (Currently amended) A glass ceramic sintered body according to claim 8, ~~further containing~~ comprising alumina as a crystal phase.

10. (Original) A glass ceramic sintered body according to claim 9, wherein the flexural strength is not smaller than 200 MPa, and a reduction in the weight of when immersed in a 1-mass % HF aqueous solution for one minute is not larger than 3  $\mu\text{g}/\text{mm}^2$ .

11. (Original) A glass ceramic sintered body according to claim 10, wherein a CaO-releasing Ca compound powder, a cordierite powder and an alumina powder are used as said filler powders.

Appl. No. 10/692,406  
Amdt. Dated May 9, 2005  
Reply to Office Action of March 21, 2003

Attorney Docket No. 81707.0189  
Customer No.: 26021

12. (Currently amended) A glass ceramic sintered body according to claim [[5]] 8 ~~wherein the comprising~~ cordierite, enstatite and/or forsterite ~~are contained as~~ crystal phases, the content of the cordierite is not smaller than 20 mass %, and the total content of the cordierite, enstatite and/or forsterite is not smaller than 40 mass %.

13. (Currently amended) A glass ceramic sintered body according to claim 12, wherein the flexural strength is not smaller than 200 MPa, and the cordierite powder, enstatite powder and/or forsterite powder are used as said filler powders.

14-23. (Canceled)

24. (Currently amended) A wiring board having wiring layers of a low-resistance metal arranged on the front surface and/or inside of an insulating substrate made of a glass ceramic sintered body of claim [[1]] 8.

25. (Original) A wiring board according to claim 24, wherein a semiconductor device comprising chiefly silicon is arranged on the surface of said insulating substrate.

26. (Original) A wiring board according to claim 25, wherein a recessed portion is formed in the surface of said insulating substrate, and a semiconductor device comprising chiefly silicon is arranged in said recessed portion.

27. (Original) A mounted structure of a wiring board obtained by mounting a wiring board of claim 24 on the surface of a printed wiring board that has an insulating substrate containing an organic resin.